OP27A, OP27C LOW-NOISE HIGH-SPEED PRECISION OPERATIONAL AMPLIFIERS

SLOS100E - FEBRUARY 1989 - REVISED FEBRUARY 2010

 Replacements for ADI, PMI and LTC OP27 Series

Features of OP27A and OP27C:

- Maximum Equivalent Input Noise Voltage:
 3.8 nV/√Hz at 1 kHz
 5.5 nV/√Hz at 10 kHz
- Very Low Peak-to-Peak Noise Voltage at 0.1 Hz to 10 Hz ... 80 nV Typ
- Low Input Offset Voltage
 OP27A . . . 25 μV Max
 OP27C . . . 100 μV Max
- High Voltage Amplification
 OP27A . . . 1 V/μV Min
 OP27C . . . 0.7 V/μV Min

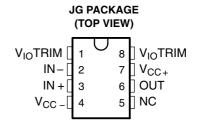
description

The OP27 operational amplifiers combine outstanding noise performance with excellent precision and high-speed specifications. The wideband noise is only 3 nV/ $\sqrt{\text{Hz}}$ and with the 1/f noise corner at 2.7 Hz, low noise is maintained for all low-frequency applications.

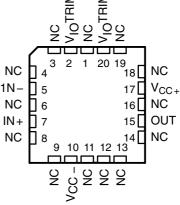
The outstanding characteristics of the OP27 make these devices excellent choices for low-noise amplifier applications requiring precision performance and reliability.

The OP27 series is compensated for unity gain.

The OP27A and OP27C are characterized for operation over the full military temperature range of -55°C to 125°C.

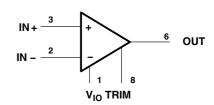






NC - No internal connection

symbol



Pin numbers are for the JG packages.

AVAILABLE OPTIONS

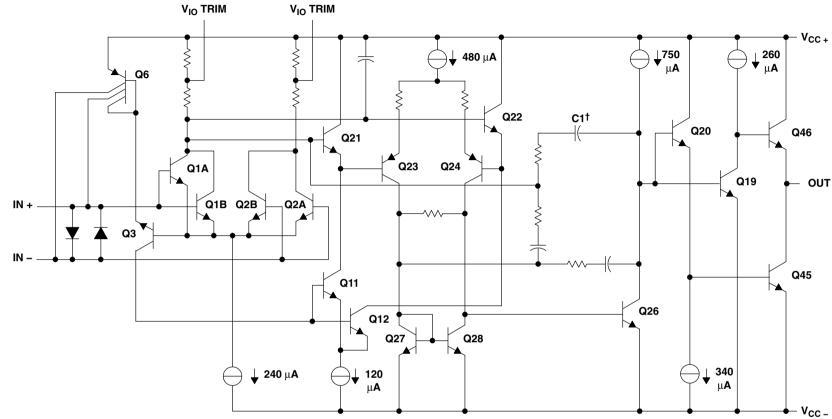
	V	CTA DI E	PACK	(AGE
T _A	V _{IO} max AT 25°C	STABLE GAIN	CERAMIC DIP (JG)	CHIP CARRIER (FK)
-55°C to 125°C	25 μV	1	OP27AJG	OP27AFK
-55 0 10 125 0	100 μV	1	OP27CJG	



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



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[†] C1 = 120 pF for OP27



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V _{CC+} (see Note 1)	22 V
Supply voltage, V _{CC} (see Note 1)	22 V
Input voltage, V _I	V _{CC±}
Duration of output short circuit	unlimited
Differential input current (see Note 2)	±25 mA
Continuous power dissipation	. See Dissipation Rating Table
Operating free-air temperature range: OP27A, OP27C	–55°C to 125°C
Storage temperature range	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: JG or FK pa	ckage 300°C

NOTES: 1. All voltage values are with respect to the midpoint between V_{CC-} and V_{CC-} unless otherwise noted.

The inputs are protected by back-to-back diodes. Current-limiting resistors are not used in order to achieve low noise. Excessive
input current will flow if a differential input voltage in excess of approximately ±0.7 V is applied between the inputs unless some
limiting resistance is used.

DISSIPATION RATING TABLE

PACKAGE	$T_A \le 25^{\circ}C$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
JG	1050 mW	8.4 mW/°C	546 mW	210 mW
FK	1375 mW	11.0 mW/°C	715 mW	275 mW

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recommended operating conditions

			OP27A			OP27C		
		MIN	NOM	MAX	MIN	NOM	MAX	UNIT
Supply voltage, V _{CC+}	4	15	22	4	15	22	V	
Supply voltage, V _{CC} _	-4	-15	-22	-4	-15	-22	V	
O	$V_{CC\pm} = \pm 15 \text{ V}, T_A = 25^{\circ}\text{C}$	± 11			±11			.,
Common-mode input voltage, V _{IC}	$V_{CC\pm} = \pm 15 \text{ V}, T_A = -55^{\circ}\text{C to } 125^{\circ}\text{C}$	±10.3			±10.2			V
Operating free-air temperature, TA	-55		125	-55		125	°C	

electrical characteristics at specified free-air temperature, $V_{CC\pm}$ = ± 15 V (unless otherwise noted)

					OP27A			OP27C				
	PARAMETER	TEST CO	ONDITIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
.,	lowed offeet valtage	$V_{O} = 0$,	V _{IC} = 0	25°C		10	25		30	100		
V_{IO}	Input offset voltage	$R_S = 50 \Omega$,	See Note 3	Full range			60			300	μV	
α_{VIO}	Average temperature coefficient of input offset voltage			Full range		0.2	0.6		0.4	1.8	μV/°C	
	Long-term drift of input offset voltage	See Note 4				0.2	1		0.4	2	μV/mo	
,	Input offset current	V _O = 0,	V _{IC} = 0	25°C		7	35		12	75	nA	
I _{IO}	input onset current	v _O = 0,	v _{IC} = 0	Full range			50			135	IIA	
l	Input bias current	V _O = 0,	V 0	25°C		±10	±40		±15	±80	nA	
I _{IB}	input bias current	v _O = 0,	v _{IC} = 0	Full range			±60			±150	150 nA	
Common-mode input				25°C	11 to –11			11 to –11			V	
VICH \	voltage range			Full range	10.3 to -10.3			10.5 to -10.5			v	
		$R_L \geq 2~k\Omega$			±12	±13.8		±11.5	±13.5			
V_{OM}	Peak output voltage swing	$R_L \ge 0.6 \ k\Omega$			±10	±11.5		±10	±11.5		V	
		$R_L \geq 2~k\Omega$		Full range	±11.5			10.5				
			$V_O = \pm 10 \text{ V}$		1000	1800		700	1500			
	Large-signal differential		$V_O = \pm 10 \text{ V}$		800	1500			1500			
A _{VD}	voltage amplification	$R_L \ge 0.6 \text{ k}\Omega$ $V_{CC\pm} = \pm 4$	$V_{O} = \pm 1 V,$		250	250 700		200	500		V/mV	
		$R_L \ge 2 k\Omega$,	$V_O = \pm 10 \text{ V}$	Full range	600			300				
r _{i(CM)}	Common-mode input resistance					3			2		GΩ	
ro	Output resistance	$V_O = 0$,	I _O = 0	25°C		70			70		Ω	
CMRR	Common-mode rejection	V _{IC} = ±11 V		25°C	114	126		100	120		-ID	
CIVINK	ratio	$V_{IC} = \pm 10 \text{ V}$	1	Full range	110			94			dB	
kova	Supply voltage rejection	$V_{CC\pm} = \pm 4$		25°C	100	120		94	118		dB	
k _{SVR}	ratio	$V_{CC\pm} = \pm 4.5$	5 V to ±18 V	Full range	96			86			מט	

 $^{^{\}dagger}$ Full range is – 55°C to 125°C.

NOTES: 3. Input offset voltage measurements are performed by automatic test equipment approximately 0.5 seconds after applying power.

^{4.} Long-term drift of input offset voltage refers to the average trend line of offset voltage versus time over extended periods after the first 30 days of operation. Excluding the initial hour of operation, changes in V_{IO} during the first 30 days are typically 2.5 μV (see Figure 3).



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OP27 operating characteristics, V_{CC^\pm} = ± 15 V, T_A = $25^{\circ}C$

	DADAMETED	TEST CONDITIONS		OP27A			OP27C			
PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	UNIT
SR	Slew rate	$A_{VD} \geq 1, \\$	$R_L \ge 2 \ k\Omega$	1.7	2.8		1.7	2.8		V/µs
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 10 Hz, See Figure 26	$R_S = 20 \Omega$,		0.225	0.375		0.225	0.375	μV
V	Facility along the set water water	f = 10 Hz,	$R_S = 20 \Omega$		3.5	8		3.8	8	VII /III
V _n	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$		3	4		3.2	4	nV/√ Hz
	Facilitation of males assument	f = 10 Hz,	See Figure 27		5	25		5	25	- A /-/III=
'n	Equivalent input noise current	f = 1 kHz,	See Figure 27		0.7	2.5		0.7	2.5	pA/√ Hz
	Gain-bandwidth product	f = 100 kHz		5	8		5	8		MHz

Table of Graphs

			FIGURE
V _{IO}	Input offset voltage	vs Temperature	1
ΔV_{IO}	Change in input offset voltage	vs Time after power on vs Time (long-term drift)	2 3
I _{IO}	Input offset current	vs Temperature	4
I _{IB}	Input bias current	vs Temperature	5
V _{ICR}	Common-mode input voltage range	vs Supply voltage	6
V _{OM}	Maximum peak output voltage	vs Load resistance	7
V _{O(PP)}	Maximum peak-to-peak output voltage	vs Frequency	8
A _{VD}	Differential voltage amplification	vs Supply voltage vs Load resistance vs Frequency	9 10 11, 12
CMRR	Common-mode rejection ratio	vs Frequency	13
k _{SVR}	Supply voltage rejection ratio	vs Frequency	14
SR	Slew rate	vs Temperature	15
φ _m	Phase margin	vs Temperature	16
ф	Phase shift	vs Frequency	11
V _n	Equivalent input noise voltage	vs Bandwidth vs Source resistance vs Supply voltage vs Temperature vs Frequency	17 18 19 20 21
	Gain-bandwidth product	vs Temperature	16
los	Short-circuit output current	vs Time	22
Icc	Supply current	vs Supply voltage	23
	Pulse response	Small signal Large signal	24 25

REPRESENTATIVE INDIVIDUAL UNITS FREE-AIR TEMPERATURE 100 $V_{CC\pm} = \pm 15 \text{ V}$ 80 OP27C 60 V_{IO} – Input Offset Voltage – μ V OP27A 40 OP27A 20 0 - 20 - 40 OP27C - 60 - 80

- 100 L - 50

- 25

INPUT OFFSET VOLTAGE OF

WARM-UP CHANGE IN INPUT OFFSET VOLTAGE VS ELAPSED TIME

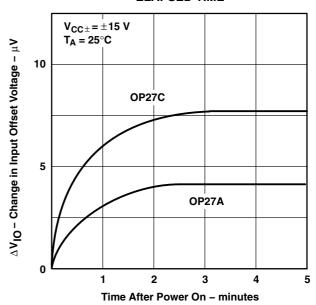


Figure 1

T_A - Free-Air Temperature - °C

Figure 2

LONG-TERM DRIFT OF INPUT OFFSET VOLTAGE OF REPRESENTATIVE INDIVIDUAL UNITS

100

125

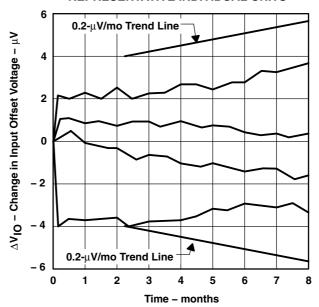
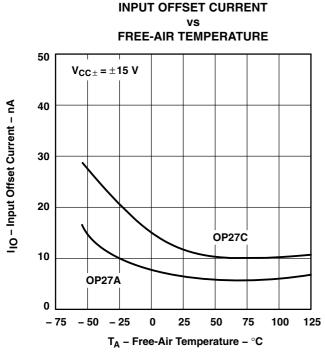


Figure 3



IB - Input Bias Current - nA $\pm\,20$ OP27C ± 10 OP27A - 75 - 50 - 25 25 50 75 T_A – Free-Air Temperature – $^{\circ}C$

 $\pm\,$ 50

 \pm 40

 $\pm\,$ 30

 $V_{CC\pm} = \pm 15 \text{ V}$

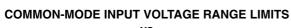
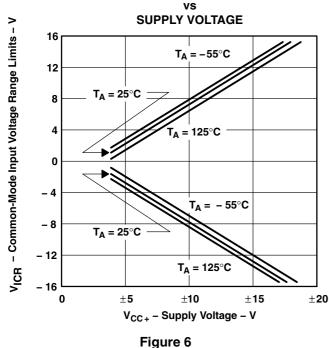


Figure 4



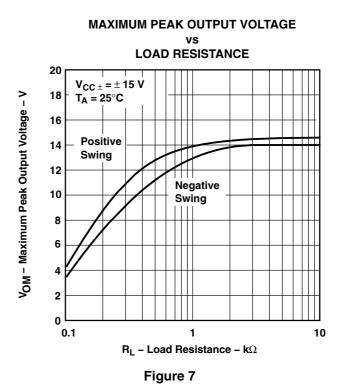


Figure 5

INPUT BIAS CURRENT

FREE-AIR TEMPERATURE

100

125

OP27 MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE

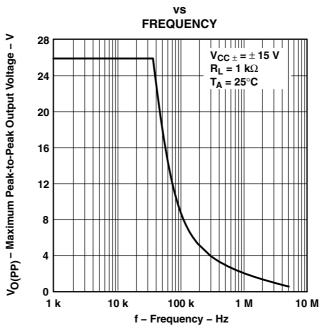


Figure 8.

OP27A LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION VS

TOTAL SUPPLY VOLTAGE

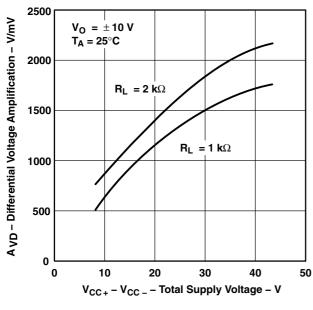


Figure 9

OP27A LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION

vs LOAD RESISTANCE

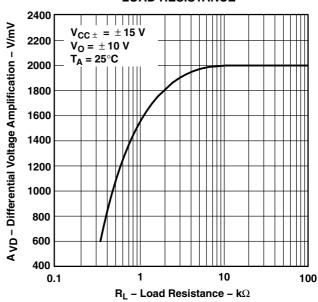


Figure 10



OP27 LARGE-SIGNAL DIFFERENTIAL **VOLTAGE AMPLIFICATION AND PHASE SHIFT**

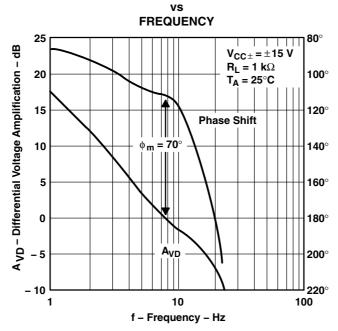


Figure 11.

OP27A LARGE-SIGNAL **DIFFERENTIAL VOLTAGE AMPLIFICATION**

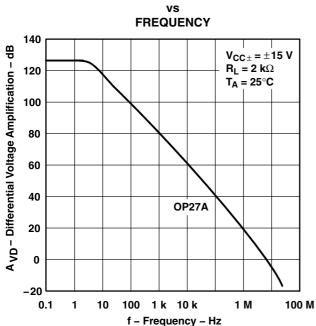


Figure 12

OP27A **COMMON-MODE REJECTION RATIO** VS

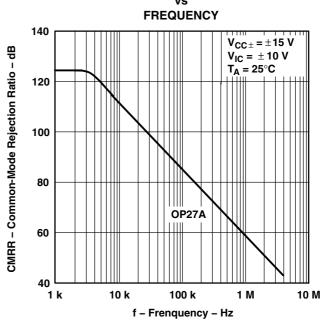


Figure 13

SUPPLY VOLTAGE REJECTION RATIO **FREQUENCY** 160 $V_{CC\pm} = \pm 4 \text{ V to } \pm 18 \text{ V}$ kSVR - Supply Voltage Rejection Ratio - dB $T_A = 25^{\circ}C$ 140 120 100 Negative Supply 80 60 40 **Positive** Supply 20 0 10 1k 10k 100k 1M 10M 100M 100 f - Frequency - Hz

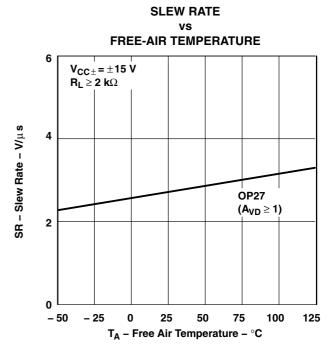


Figure 14

Figure 15

OP27 PHASE MARGIN AND GAIN-BANDWIDTH PRODUCT

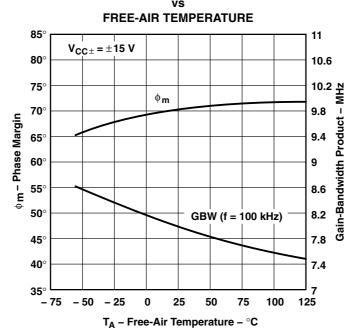


Figure 16.

EQUIVALENT INPUT NOISE VOLTAGE vs BANDWIDTH

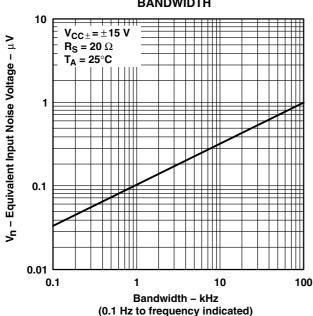


Figure 17 OP27A EQUIVALENT INPUT NOISE VOLTAGE VS TOTAL SUPPLY VOLTAGE

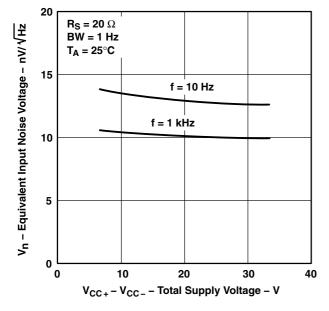


Figure 19

TOTAL EQUIVALENT INPUT NOISE VOLTAGE

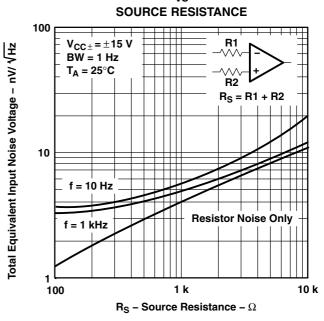


Figure 18

OP27A

EQUIVALENT INPUT NOISE VOLTAGE

vs

FREE-AIR TEMPERATURE

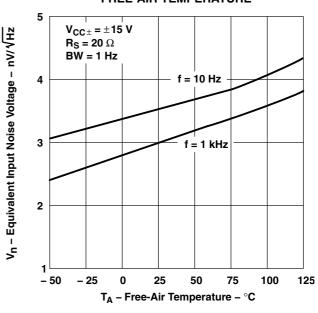


Figure 20

OP27A EQUIVALENT INPUT NOISE VOLTAGE vs

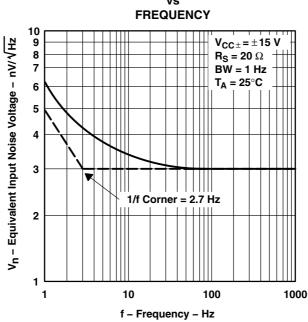


Figure 21

SHORT-CIRCUIT OUTPUT CURRENT

vs **ELAPSED TIME** 60 $V_{CC\pm}$ = \pm 15 V $T_A = 25^{\circ}C$ IOS - Short-Circuit Output Current - mA 50 los-40 30 los+ 20 10 3 4 0 5 t - Time - minutes

Figure 22

SUPPLY CURRENT vs

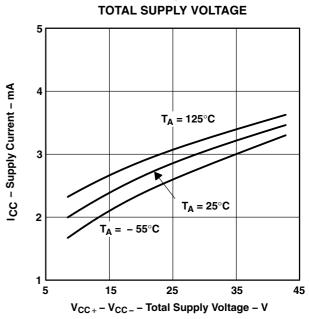
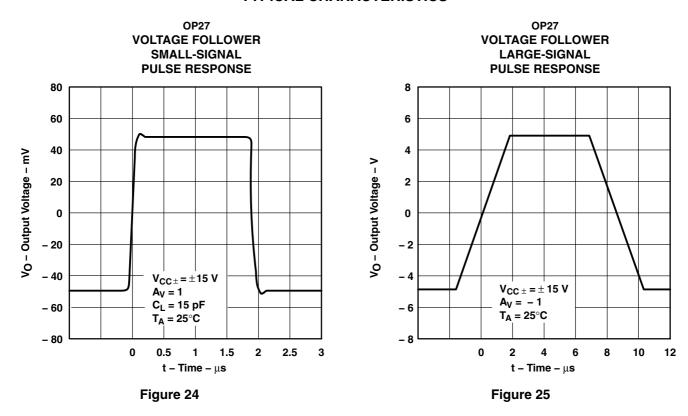


Figure 23

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TYPICAL CHARACTERISTICS



APPLICATION INFORMATION

general

The OP27 series devices can be inserted directly onto OP07, OP05, μ A725, and SE5534 sockets with or without removing external compensation or nulling components. In addition, the OP27 can be fitted to μ A741 sockets by removing or modifying external nulling components.

noise testing

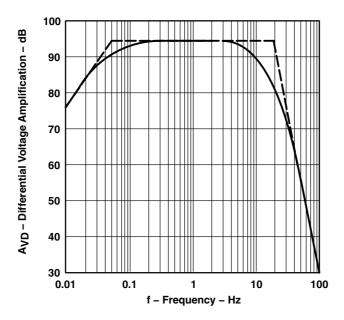
Figure 26 shows a test circuit for 0.1-Hz to 10-Hz peak-to-peak noise measurement of the OP27. The frequency response of this noise tester indicates that the 0.1-Hz corner is defined by only one zero. Because the time limit acts as an additional zero to eliminate noise contributions from the frequency band below 0.1 Hz, the test time to measure 0.1-Hz to 10-Hz noise should not exceed 10 seconds.

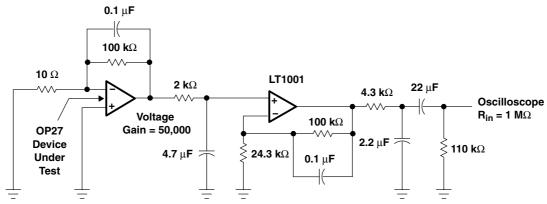
Measuring the typical 80-nV peak-to-peak noise performance of the OP27 requires the following special test precautions:



noise testing (continued)

- 1. The device should be warmed up for at least five minutes. As the operational amplifier warms up, the offset voltage typically changes 4 μ V due to the chip temperature increasing from 10°C to 20°C starting from the moment the power supplies are turned on. In the 10-s measurement interval, these temperature-induced effects can easily exceed tens of nanovolts.
- 2. For similar reasons, the device should be well shielded from air currents to eliminate the possibility of thermoelectric effects in excess of a few nanovolts, which would invalidate the measurements.
- 3. Sudden motion in the vicinity of the device should be avoided, as it produces a feedthrough effect that increases observed noise.





NOTE: All capacitor values are for nonpolarized capacitors only.

Figure 26. 0.1-Hz to 10-Hz Peak-to-Peak Noise Test Circuit and Frequency Response



noise testing (continued)

When measuring noise on a large number of units, a noise-voltage density test is recommended. A 10-Hz noise-voltage density measurement correlates well with a 0.1-Hz to 10-Hz peak-to-peak noise reading since both results are determined by the white noise and the location of the 1/f corner frequency.

Figure 27 shows a circuit measuring current noise and the formula for calculating current noise.

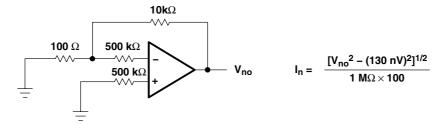


Figure 27. Current Noise Test Circuit and Formula

offset voltage adjustment

The input offset voltage and temperature coefficient of the OP27 are permanently trimmed to a low level at wafer testing. However, if further adjustment of V_{IO} is necessary, using a 10-k Ω nulling potentiometer as shown in Figure 28 does not degrade the temperature coefficient α_{VIO} . Trimming to a value other than zero creates an α_{VIO} of $V_{IO}/300~\mu V/^{\circ}C$. For example, if V_{IO} is adjusted to 300 μV , the change in α_{VIO} is 1 $\mu V/^{\circ}C$.

The adjustment range with a 10-k Ω potentiometer is approximately ± 2.5 mV. If a smaller adjustment range is needed, the sensitivity and resolution of the nulling can be improved by using a smaller potentiometer in conjunction with fixed resistors. The example in Figure 29 has an approximate null range of $\pm 200 \,\mu\text{V}$.

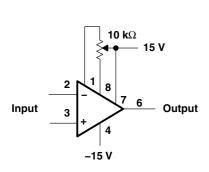


Figure 28. Standard Input Offset Voltage Adjustment

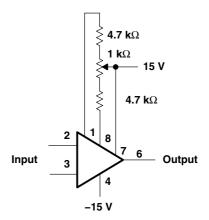


Figure 29. Input Offset Voltage Adjustment With Improved Sensitivity

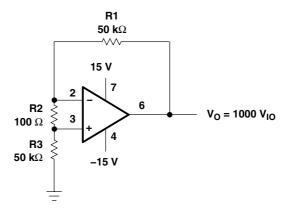
offset voltage and drift

Unless proper care is exercised, thermoelectric effects caused by temperature gradients across dissimilar metals at the contacts to the input terminals can exceed the inherent temperature coefficient ${}^{\infty}V_{IO}$ of the amplifier. Air currents should be minimized, package leads should be short, and the two input leads should be close together and at the same temperature.



offset voltage and drift (continued)

The circuit shown in Figure 30 measures offset voltage. This circuit can also be used as the burn-in configuration for the OP27 with the supply voltage increased to 20 V, R1 = R3 = 10 k Ω , R2 = 200 Ω , and A_{VD} = 100.



NOTE A: Resistors must have low thermoelectric potential.

Figure 30. Test Circuit for Offset Voltage and Offset Voltage Temperature Coefficient

unity gain buffer applications

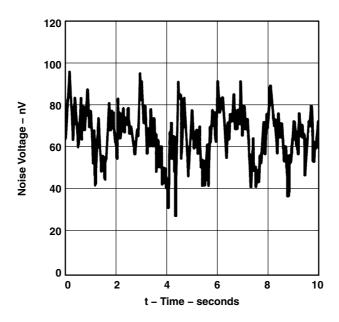
The resulting output waveform, when $R_f \le 100 \Omega$ and the input is driven with a fast large-signal pulse (>1 V), is shown in the pulsed-operation diagram in Figure 31.



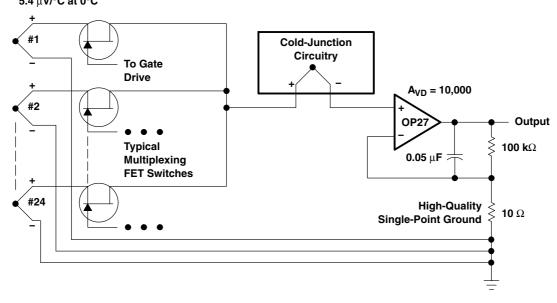
Figure 31. Pulsed Operation

During the initial (fast-feedthrough-like) portion of the output waveform, the input protection diodes effectively short the output to the input, and a current, limited only by the output short-circuit protection, is drawn by the signal generator. When $R_f \geq 500~\Omega$, the output is capable of handling the current requirements (load current $\leq\!20$ mA at 10 V), the amplifier stays in its active mode, and a smooth transition occurs. When $R_f > 2~k\Omega$, a pole is created with R_f and the amplifier's input capacitance, creating additional phase shift and reducing the phase margin. A small capacitor (20 pF to 50 pF) in parallel with R_f eliminates this problem.

unity gain buffer applications (continued)



Type S Thermocouples 5.4 μ V/°C at 0°C



NOTE A: If 24 channels are multiplexed per second and the output is required to settle to 0.1 % accuracy, the amplifier's bandwidth cannot be limited to less than 30 Hz. The peak-to-peak noise contribution of the OP27 will still be only 0.11 μV, which is equivalent to an error of only 0.02°C.

Figure 32. Low-Noise, Multiplexed Thermocouple Amplifier and 0.1-Hz to 10-Hz Peak-to-Peak Noise Voltage







31-May-2014

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_		Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
JM38510/13506BPA	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	JM38510 /13506BPA	Samples
M38510/13506BPA	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	JM38510 /13506BPA	Samples
OP27AFKB	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	-55 to 125	OP27AFKB	Samples
OP27AJGB	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	OP27AJGB	Samples
OP27CJGB	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type	-55 to 125	OP27CJGB	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.



PACKAGE OPTION ADDENDUM

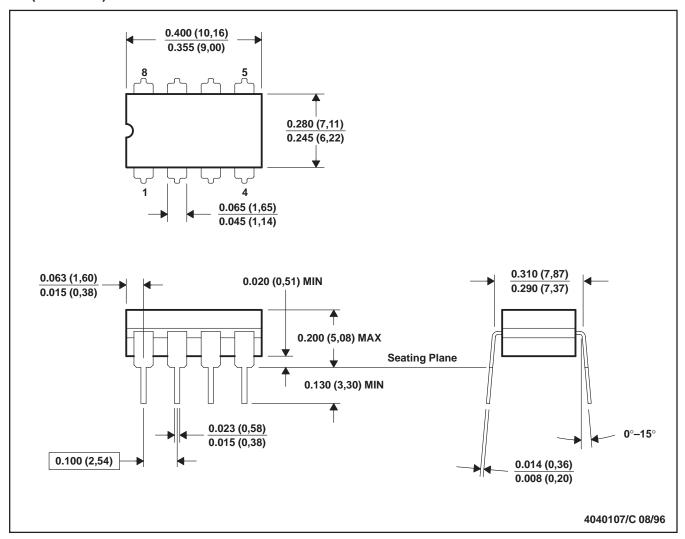
31-May-2014

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JG (R-GDIP-T8)

CERAMIC DUAL-IN-LINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification.
- E. Falls within MIL STD 1835 GDIP1-T8

FK (S-CQCC-N**)

LEADLESS CERAMIC CHIP CARRIER

28 TERMINAL SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. Falls within JEDEC MS-004



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